

GENERAL DESCRIPTION

The 83058I is a low skew, 8:1, Single-ended Multiplexer and a member of the family of High Performance Clock Solutions from IDT. The 83058I has eight selectable single-ended clock inputs and one single-ended clock output. The output has a $V_{\mbox{\tiny DDO}}$ pin which may be set at 3.3V, 2.5V, or 1.8V, making the device ideal for use in voltage translation applications. An output enable pin places the output in a high impedance state which may be useful for testing or debug purposes. The device operates up to 250MHz and is packaged in a 16 TSSOP package.

FEATURES

- 8:1 single-ended multiplexer
- Q nominal output impedance: $7\Omega (V_{DDO} = 3.3V)$
- · Maximum output frequency: 250MHz
- Propagation delay: 3ns (maximum), V_{DD} = V_{DDD} = 3.3V
- Input skew: 225ps (maximum), $V_{DD} = V_{DDO} = 3.3V$
- Part-to-part skew: 475ps (maximum), V_{DD} = V_{DDQ} = 3.3V
- Additive phase jitter, RMS: 0.19ps (typical), 3.3V/3.3V
- · Operating supply modes:

V_{DD}/V_{DDO} 3.3V/3.3V

3.3V/2.5V

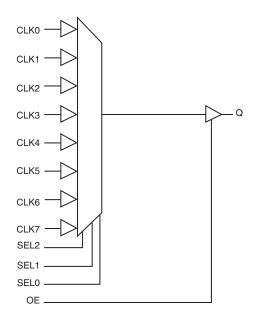
3.3V/1.8V

2.5V/2.5V

2.5V/1.8V

- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

BLOCK DIAGRAM



PIN ASSIGNMENT



83058I 16-Lead TSSOP 4.4mm x 5.0mm x 0.92mm package body G Package Top View



TABLE 1. PIN DESCRIPTIONS

Number	Name	Т	уре	Description
1	Q	Output		Single-ended clock output. LVCMOS/LVTTL interface levels.
2, 4, 6, 8, 9, 11, 13, 15	CLK7, CLK6, CLK5, CLK4, CLK3, CLK2, CLK1, CLK0	Input	Pulldown	Single-ended clock inputs. LVCMOS/LVTTL interface levels.
3	OE	Input	Pullup	Output enable. When LOW, outputs are in HIGH impedance state. When HIGH, outputs are active. LVCMOS / LVTTL interface levels.
5	GND	Power		Power supply ground.
7, 10, 14	SEL2, SEL1, SEL0	Input	Pulldown	Clock select input. See Control Input Function Table. LVCMOS / LVTTL interface levels.
12	V _{DD}	Power		Core and input supply pin.
16	V _{DDO}	Power		Output supply pin.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R	Input Pullup Resistor			51		kΩ
R	Input Pulldown Resistor			51		kΩ
		V _{DDO} = 3.465V		18		pF
C _{PD}	Power Dissipation Capacitance (per output)	$V_{_{DDO}} = 2.625V$		20		pF
	(per output)	V _{DDO} = 1.89V		30		pF
		V _{DDO} = 3.465V		7		Ω
R _{out}	Output Impedance	V _{DDO} = 2.625V		7		Ω
		V _{DDO} = 1.89V		10		Ω

TABLE 3. CONTROL INPUT FUNCTION TABLE

	Control Inputs		Input Selected to Q
SEL2	SEL1	SEL0	input Selected to Q
0	0	0	CLK0
0	0	1	CLK1
0	1	0	CLK2
0	1	1	CLK3
1	0	0	CLK4
1	0	1	CLK5
1	1	0	CLK6
1	1	1	CLK7



ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V_{DD} 4.6V

 $\begin{array}{ll} \text{Inputs, V}_{_{_{\! O}}} & -0.5 \text{V to V}_{_{\! DD}} + 0.5 \text{ V} \\ \\ \text{Outputs, V}_{_{\! O}} & -0.5 \text{V to V}_{_{\! DDO}} + 0.5 \text{V} \\ \\ \text{Package Thermal Impedance, } \theta_{_{\! A}} & 89^{\circ}\text{C/W (0 lfpm)} \end{array}$

Storage Temperature, T_{ste} -65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 4A. Power Supply DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Power Supply Voltage		3.135	3.3	3.465	V
V	Output Supply Voltage		3.135	3.3	3.465	V
I _{DD}	Power Supply Current				40	mA
I _{DDO}	Output Supply Current				5	mA

Table 4B. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDD} = 2.5V \pm 5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Power Supply Voltage		3.135	3.3	3.465	V
V	Output Supply Voltage		2.375	2.5	2.625	V
I _{DD}	Power Supply Current				40	mA
I _{DDO}	Output Supply Current				5	mA

Table 4C. Power Supply DC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.8V \pm 0.2V$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V	Power Supply Voltage		3.135	3.3	3.465	V
V _{DDO}	Output Supply Voltage		1.71	1.8	1.89	V
l _{DD}	Power Supply Current				40	mA
 DDO	Output Supply Current				5	mA

Table 4D. Power Supply DC Characteristics, $V_{dd} = V_{ddd} = 2.5V \pm 5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Power Supply Voltage		2.375	2.5	2.625	V
V	Output Supply Voltage		2.375	2.5	2.625	V
l _{DD}	Power Supply Current				35	mA
I _{DDO}	Output Supply Current				5	mA

Table 4E. Power Supply DC Characteristics, $V_{dd} = 2.5V \pm 5\%$, $V_{ddd} = 1.8V \pm 0.2V$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Power Supply Voltage		2.375	2.5	2.625	V
V	Output Supply Voltage		1.71	1.8	1.89	V
I _{DD}	Power Supply Current				35	mA
I _{DDO}	Output Supply Current				5	mA



Table 4F. LVCMOS/LVTTL DC Characteristics, TA = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
\/	Input High Voltage		$V_{_{DD}} = 3.3V \pm 5\%$	2		V _{DD} + 0.3	V
V _{IH}	Input High Voltage		$V_{DD} = 2.5V \pm 5\%$	1.7		V _{DD} + 0.3	V
\/	Input Low Voltage		$V_{_{DD}} = 3.3V \pm 5\%$	-0.3		0.8	V
V _{IL}	Input Low Voltage		$V_{DD} = 2.5V \pm 5\%$	-0.3		0.7	V
I	Input High Current	CLK0:CLK5, SEL0:SEL2	$V_{DD} = 3.3V \text{ or } 2.5V \pm 5\%$			150	μA
IH IH		OE	$V_{DD} = 3.3 \text{V or } 2.5 \text{V} \pm 5\%$			5	μΑ
I _{II}	Input Low Current	CLK0:CLK5, SEL0:SEL2	$V_{DD} = 3.3V \text{ or } 2.5V \pm 5\%$	-5			μA
		OE	$V_{DD} = 3.3 \text{V or } 2.5 \text{V} \pm 5\%$	-150			μΑ
			$V_{_{\rm DDO}} = 3.3V \pm 5\%; \text{ NOTE 1}$	2.6			V
V _{OH}	Output HighVoltage	•	$V_{DDO} = 2.5V \pm 5\%$; NOTE 1	1.8			V
			$V_{DDO} = 1.8V \pm 5\%; NOTE 1$	V _{DD} - 0.3			V
	Output Low Voltage		$V_{_{\rm DDO}} = 3.3 \text{V} \pm 5\%; \text{ NOTE 1}$			0.5	V
V _{OL}			$V_{_{\rm DDO}} = 2.5 \text{V} \pm 5\%; \text{ NOTE 1}$			0.45	V
			$V_{_{\rm DDO}} = 1.8V \pm 5\%; \text{ NOTE 1}$			0.35	V

NOTE 1: Outputs terminated with 50Ω to V_{DDD}/2. See Parameter Measurement section, "Load Test Circuit" diagrams.

Table 5A. AC Characteristics, $V_{_{DD}} = V_{_{DDO}} = 3.3V \pm 5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp_	Propagation Delay, Low to High; NOTE 1		1.8	2.4	3.0	ns
tp _{HL}	Propagation Delay, High to Low; NOTE 1		2.5	2.7	2.9	ns
tsk(i)	Input Skew; NOTE 2			55	225	ps
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 3	155.52MHz, (12kHz to 20MHz)		0.19		ps
tsk(pp)	Part-to-Part Skew; NOTE 2, 4				475	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	50		500	ps
odc	Output Duty Cycle		45		55	%
MUX	MUX Isolation	@ 100MHz		45		dB

NOTE 1: Measured from $V_{DD}/2$ of the input to $V_{DDD}/2$ of the output. NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Driving only one input clock.

NOTE 4: Defined as skew between outputs on different devices operating a the same supply voltages and with equal load conditions. Using the same type of input on each device, the output is measured at $V_{poo}/2$.



Table 5B. AC Characteristics, $V_{dd} = 3.3V \pm 5\%$, $V_{ddd} = 2.5V \pm 5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp_LH	Propagation Delay, Low to High; NOTE 1		2.0	2.5	3.1	ns
tp _{HL}	Propagation Delay, High to Low; NOTE 1		2.6	2.8	3.0	ns
tsk(i)	Input Skew; NOTE 2			45	150	ps
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 3	155.52MHz, (12kHz to 20MHz)		0.14		ps
tsk(pp)	Part-to-Part Skew; NOTE 2, 4				400	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	50		500	ps
odc	Output Duty Cycle		45		55	%
MUX	MUX Isolation	@ 100MHz		45		dB

NOTE 1: Measured from $V_{_{DD}}/2$ of the input to $V_{_{DDO}}/2$ of the output. NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Driving only one input clock.

NOTE 4: Defined as skew between outputs on different devices operating a the same supply voltages and with equal load conditions. Using the same type of input on each device, the output is measured at V₂₀₀/2.

Table 5C. AC Characteristics, $V_{DD} = 3.3V \pm 5\%$, $V_{DDO} = 1.8V \pm 5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp	Propagation Delay, Low to High; NOTE 1		2.3	2.9	3.8	ns
tp _{HL}	Propagation Delay, High to Low; NOTE 1		2.8	3.3	3.8	ns
tsk(i)	Input Skew; NOTE 2			50	150	ps
<i>t</i> jit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 3	155.52MHz, (12kHz to 20MHz)		0.16		ps
tsk(pp)	Part-to-Part Skew; NOTE 2, 4				475	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	100		700	ps
odc	Output Duty Cycle		45		55	%
MUX	MUX Isolation	@ 100MHz		45		dB

NOTE 1: Measured from V_{DD}/2 of the input to V_{DDD}/2 of the output. NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Driving only one input clock.

NOTE 4: Defined as skew between outputs on different devices operating a the same supply voltages and with equal load conditions. Using the same type of input on each device, the output is measured at $V_{ppo}/2$.



Table 5D. AC Characteristics, $V_{DD} = V_{DDD} = 2.5V \pm 5\%$, $TA = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp_	Propagation Delay, Low to High; NOTE 1		1.9	2.7	3.5	ns
tp _{HL}	Propagation Delay, High to Low; NOTE 1		2.5	2.9	3.4	ns
tsk(i)	Input Skew; NOTE 2			60	175	ps
tjit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 3	155.52MHz, (12kHz to 20MHz)		0.21		ps
tsk(pp)	Part-to-Part Skew; NOTE 2, 4				300	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	100		500	ps
odc	Output Duty Cycle		40		60	%
MUX	MUX Isolation	@ 100MHz		45		dB

NOTE 1: Measured from $V_{\tiny DD}/2$ of the input to $V_{\tiny DDD}/2$ of the output. NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Driving only one input clock.

NOTE 4: Defined as skew between outputs on different devices operating a the same supply voltages and with equal load conditions. Using the same type of input on each device, the output is measured at $V_{ppo}/2$.

Table 5E. AC Characteristics, $V_{DD} = 2.5V \pm 5\%$, $V_{DDD} = 1.8V \pm -5\%$, Ta = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{MAX}	Output Frequency				250	MHz
tp_	Propagation Delay, Low to High; NOTE 1		2.2	2.9	4.0	ns
tp _{HL}	Propagation Delay, High to Low; NOTE 1		2.7	3.3	4.0	ns
tsk(i)	Input Skew; NOTE 2			50	150	ps
tjit	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section; NOTE 3	155.52MHz, (12kHz to 20MHz)		0.17		ps
tsk(pp)	Part-to-Part Skew; NOTE 2, 4				325	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	100		700	ps
odc	Output Duty Cycle		40		60	%
MUX	MUX Isolation	@ 100MHz		45		dB

NOTE 1: Measured from $V_{_{DD}}/2$ of the input to $V_{_{DDO}}/2$ of the output. NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Driving only one input clock.

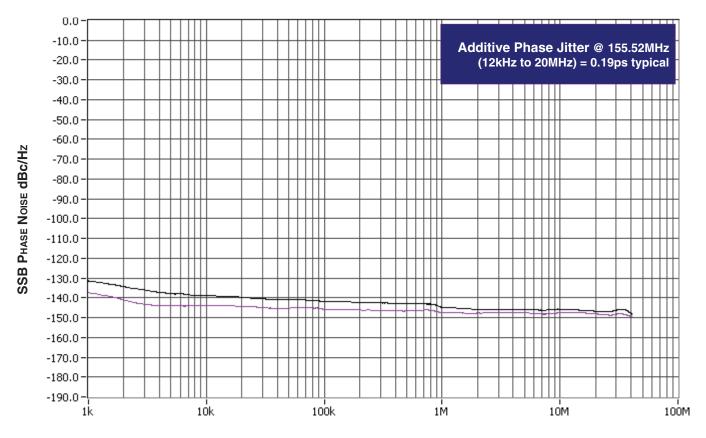
NOTE 4: Defined as skew between outputs on different devices operating a the same supply voltages and with equal load conditions. Using the same type of input on each device, the output is measured at V₂₀₀₂/2.



ADDITIVE PHASE JITTER

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the *dBc Phase Noise*. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels

(dBm) or a ratio of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a *dBc* value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.



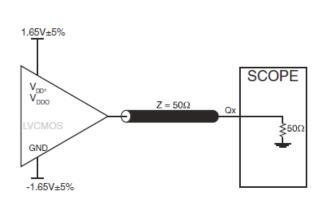
OFFSET FROM CARRIER FREQUENCY (Hz)

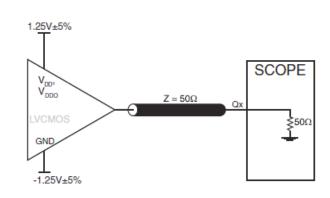
As with most timing specifications, phase noise measurements has issues relatings to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device.

This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.



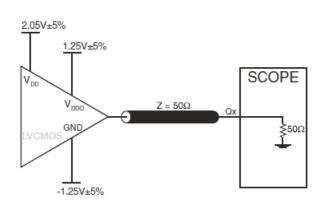
PARAMETER MEASUREMENT INFORMATION

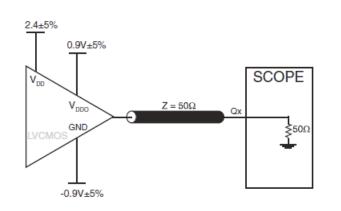




3.3V CORE/3.3V OUTPUT LOAD AC TEST CIRCUIT

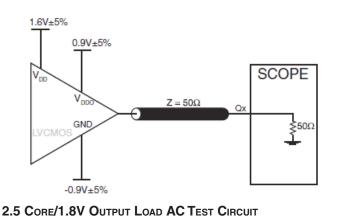
2.5V Core/2.5V Output Load AC Test Circuit

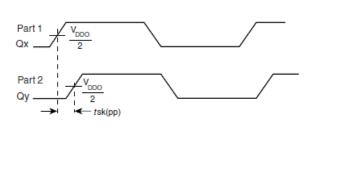




3.3V Core/2.5V OUTPUT LOAD AC TEST CIRCUIT

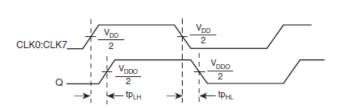
3.3V CORE/1.8V OUTPUT LOAD AC TEST CIRCUIT

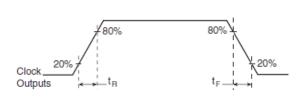




PART-TO-PART SKEW



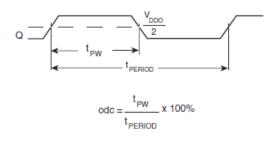




PROPAGATION DELAY

CLKy CLKy t_{PD1} t_{PD2} $t_{PD2} - t_{PD1}$

OUTPUT RISE/FALL TIME



INPUT SKEW

OUTPUT DUTY CYCLE/PULSE WIDTH/PERIOD



APPLICATION INFORMATION

RECOMMENDATIONS FOR UNUSED INPUT PINS

INPUTS:

CLK INPUTS

For applications not requiring the use of a clock input, it can be left floating. Though not required, but for additional protection, a $1 k\Omega$ resistor can be tied from the CLK input to ground.

LVCMOS CONTROL PINS

All control pins have internal pull-ups or pull-downs; additional resistance is not required but can be added for additional protection. A $1 \mbox{k}\Omega$ resistor can be used.



RELIABILITY INFORMATION

Table 6. $\theta_{,_{JA}} \text{vs. Air Flow Table for 16 Lead TSSOP}$

θ_{JA} by Velocity (Linear Feet per Minute)

 O
 200
 500

 Single-Layer PCB, JEDEC Standard Test Boards
 137.1°C/W
 118.2°C/W
 106.8°C/W

 Multi-Layer PCB, JEDEC Standard Test Boards
 89.0°C/W
 81.8°C/W
 78.1°C/W

NOTE: Most modern PCB designs use multi-layered boards. The data in the second row pertains to most designs.

TRANSISTOR COUNT

The transistor count for 83058I is: 874

PACKAGE OUTLINE AND PACKAGE DIMENSIONS

PACKAGE OUTLINE - G SUFFIX FOR 16 LEAD TSSOP

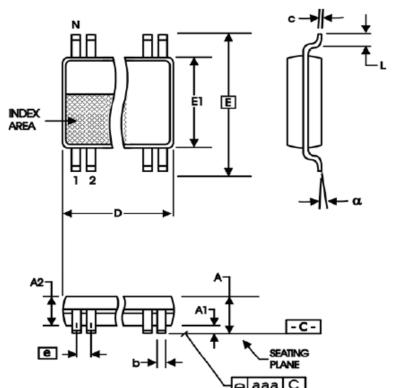


TABLE 7. PACKAGE DIMENSIONS

SYMBOL	Millimeters		
STWIBOL	Minimum	Maximum	
N	1	6	
Α		1.20	
A1	0.05	0.15	
A2	0.80	1.05	
b	0.19	0.30	
С	0.09	0.20	
D	4.90	5.10	
E	6.40 E	BASIC	
E1	4.30	4.50	
е	0.65 E	BASIC	
L	0.45	0.75	
α	0°	8°	
aaa	-	0.10	

Reference Document: JEDEC Publication 95, MO-153



Table 8. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
83058AGILF	83058AIL	16 Lead "Lead-Free" TSSOP	tube	-40°C to 85°C
83058AGILFT	83058AIL	16 Lead "Lead-Free" TSSOP	tape & reel	-40°C to 85°C



	REVISION HISTORY SHEET					
Rev	Table	Page	Description of Change	Date		
		1	Features Section - added Additive Phase Jitter bullet.			
В	T5A - T5E	4 - 6	AC Characteristics Tables - added tjit row and spec.	01/04/07		
		7	Added Additive Phase Jitter section.			
	T5A - T5E	4 - 6	AC Characteristics Tables - changed minimum and typical propagation delay			
С			specs.	03/10/08		
	T8	12	Ordering Information Table - added lead-free marking.			
D	T8	12	Ordering information - removed leaded devices and removed ICS in the Part/Order Number.	11/21/14		
0			Updated datasheet format	11/21/14		
		1	General Description - removed HiPerClockS.			
D	T8	12	Ordering Information - removed 2500 from Tape and Reel. Removed LF note below the table.	12/15/15		
			Updated Header and Footer.			



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